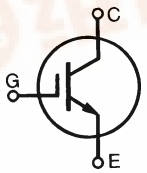
IXYS

Preliminary data

High Speed IGBT

Short Circuit SOA Capability

	V_{CES}	$I_{C(25)}$	$V_{CE(sat)}$
IXSH10N60	600 V	20 A	2.5 V
IXSH10N60A	600 V	20 A	3.0 V



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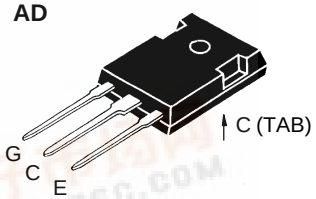


G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	20	A
I_{C90}	T_C = 90°C	10	A
I_{CM}	T_C = 25°C, 1 ms	40	A
SSOA (RBSOA)	V_{GE}= 15 V, T_J = 125°C, R_G = 150 Ω Clamped inductive load, L = 300 µH	I_{CM} = 20 @ 0.8 V_{CES}	A
t_{SC} **(SCSOA)**	V_{GE}= 15 V, V_{CE} = 360 V, T_J = 125°C R_G = 82 Ω, non repetitive	10	µs
P_C	T_C = 25°C	100	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight			6 g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250 µA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 750 µA, V_{CE} = V_{GE}		3.5		6.5	V
I_{CES}	V_{CE} = 0.8 • V_{CES} V_{GE} = 0 V	T_J = 25°C T_J = 125°C			200 1	µA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V	10N60 10N60A			2.5 3.0	V V

Features

- International standard packages
- Guaranteed Short Circuit SOA capability
- Low $V_{CE(sat)}$
  - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
  - drive simplicity
- Fast Fall Time for switching speeds up to 20 kHz

Applications

- AC motor speed control
- Uninterruptible power supplies (UPS)
- Welding

Advantages

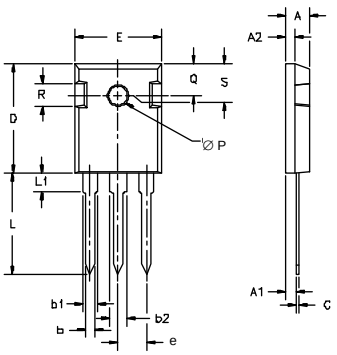
- Easy to mount with 1 screw (isolated mounting screw hole)
- High power density

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %		2			S
$I_{C(on)}$	V_{GE} = 15 V, V_{CE} = 10 V			50		A
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz			750		pF
C_{oes}				125		pF
C_{res}				30		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}			40		nC
Q_{ge}				12		nC
Q_{gc}				20	80	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**			100		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V,			200		ns
$t_{d(off)}$	L = 300 µH, V_{CE} = 0.8 V_{CES},			250	750	ns
t_{fi}	R_G = 150Ω	10N60A		175	410	ns
		10N60		720		ns
E_{off}		10N60A		0.75	1.2	mJ
	Note 1	10N60		1.2	1.9	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**			100		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V,			200		ns
E_{on}	L = 300 µH, V_{CE} = 0.8 V_{CES},			1.0		mJ
$t_{d(off)}$	R_G = 150 Ω			300		ns
t_{fi}		10N60AU1		400		ns
E_{off}	Note 1	10N60AU1		1.5		mJ
R_{thJC}					1.25	K/W
R_{thCK}				0.25		K/W

Notes: 1. Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or R_G values.

2. Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.

TO-247 AD Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

Fig.1. Output Characteristics

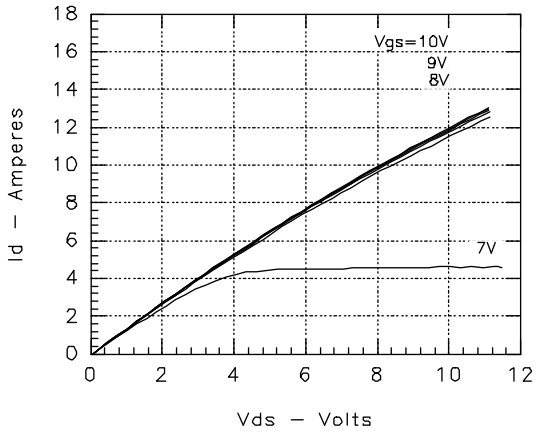


Fig. 2. Input Admittance

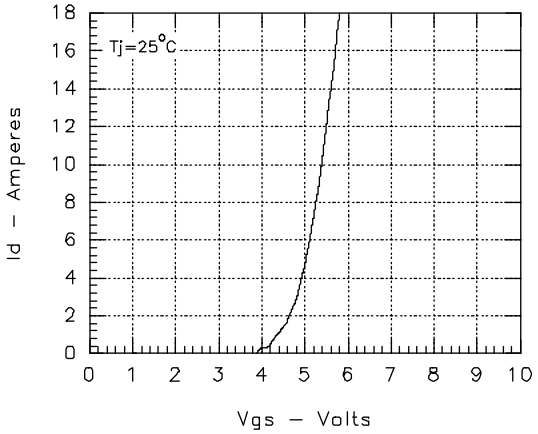


Fig. 3. Rds(on) vs. Drain Current

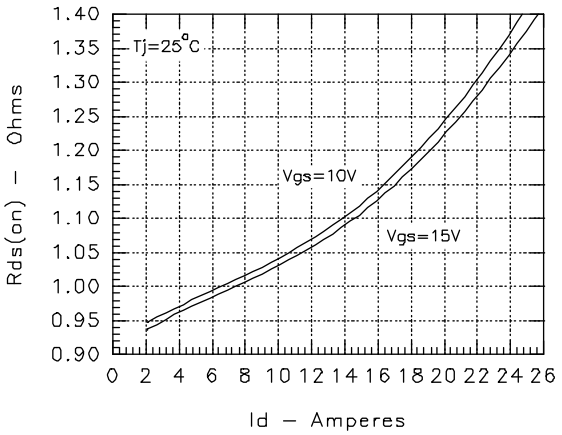


Fig. 4. Temperature Dependence of Drain to Source Resistance

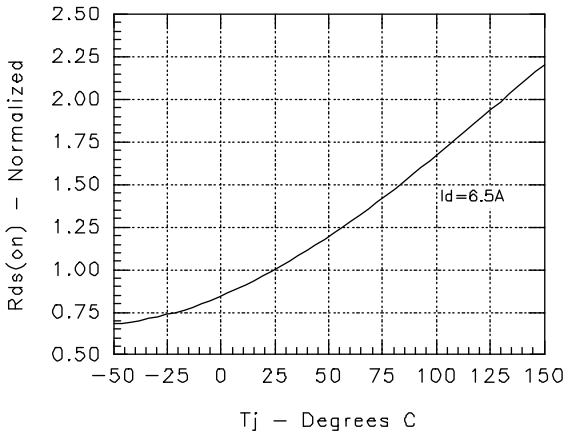


Fig. 5. Drain Current vs. Case Temperature

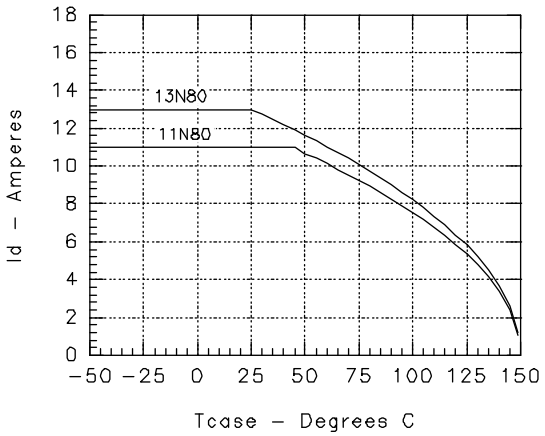


Fig. 6. Temperature Dependence of Breakdown Voltage and Threshold Voltage

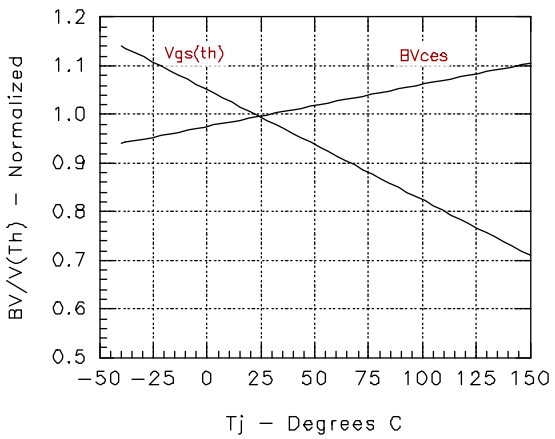


Fig. 7. Gate Charge

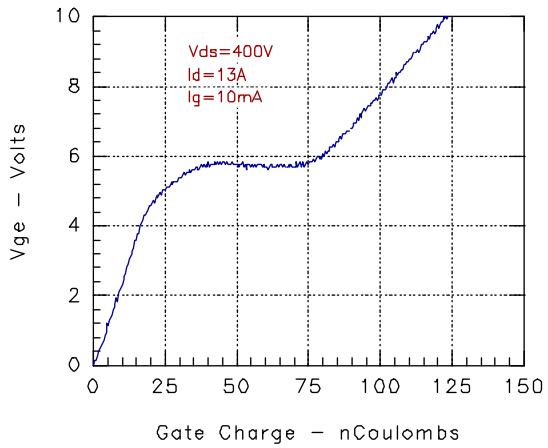


Fig. 8. Forward Bias Safe Operating Area

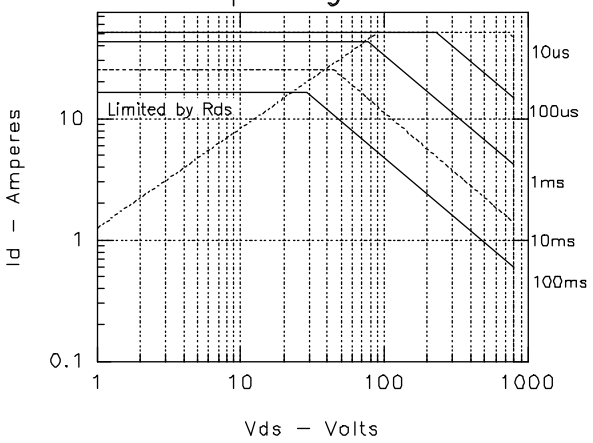


Fig. 9. Capacitance Curves

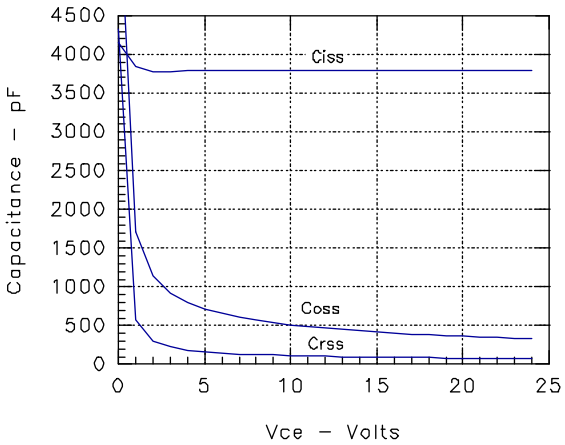


Fig. 10. Source Current vs. Source to Drain Voltage

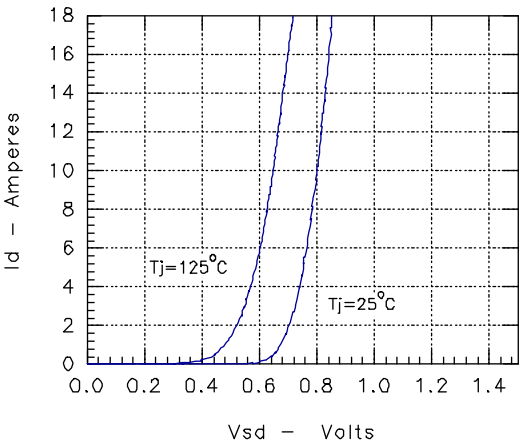


Fig. 11. Transient Thermal Impedance